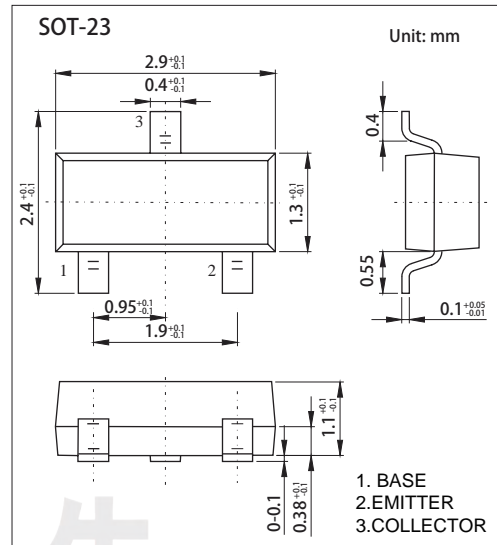


PNP Transistors MMBT3906

■ Features

- Collector current: $I_c = -0.2A$
- Complementary to MMBT3906



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-40	V
Collector - Emitter Voltage	V_{CE0}	-40	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_c	-200	mA
Collector Power Dissipation	P_c	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	$^\circ C/W$
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to 150	

Transistor

PNP Transistors MMBT3906

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collecto- base breakdown voltage	V _{CBO}	I _C = -10 μA, I _E =0	-40			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -1 mA, I _B =0	-40			
Emitter - base breakdown voltage	V _{EBO}	I _E = -10 μA, I _C =0	-5			
Collector cut-off current	I _{CBO}	V _{CB} = -40 V, I _E =0			-0.1	μA
Collector cut-off current	I _{CEX}	V _{CE} =-30 V, V _{BE(off)} =-3V			-0.05	
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C =0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-50 mA, I _B = -5mA			-0.3	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-50 mA, I _B = -5mA			-0.95	
DC current gain	h _{FE(1)}	V _{CE} = -1V, I _C = -10mA	100		300	
	h _{FE(2)}	V _{CE} = -1V, I _C = -50mA	60			
	h _{FE(3)}	V _{CE} = -1V, I _C = -100mA	30			
Delay time	t _d	V _{CC} =-3V, V _{BE} =-0.5V			35	ns
Rise time	t _r	I _C =-10mA, I _{B1} =I _{B2} =-1mA			35	
Storage time	t _s	V _{CC} =-3V, I _C =-10mA			225	
Fall time	t _f	I _{B1} =I _{B2} =-1mA			75	
Transition frequency	f _T	V _{CE} = -20V, I _C = -10mA, f=100MHz	300			MHz

■ Classification of h_{FE(1)}

Rank	L	H
Range	100-200	200-300
Marking	2A	

Transistor

PNP Transistors MMBT3906

Typical Characteristics

